

What is claimed is:

1. A silicon platform for optical modules comprising:
a silicon substrate;
a first insulating layer formed on the silicon substrate;
a first conductor layer formed on the first insulating layer;
a second insulating layer formed on the first conductor layer;
and
a second conductor layer formed on the second insulating layer,
an end portion of the second conductor layer overlying the first insulating layer to constitute bonding portions connected to lead wires.
2. A silicon platform for optical modules according to claim 1, wherein a hole is formed in the second insulating layer and a bonding portion is formed in this hole.
3. A silicon platform for optical modules according to claim 1, wherein a removed portion is formed in the second insulating layer and a bonding portion is formed in this removed portion.
4. A silicon platform for optical modules according to claim 1, wherein the second insulating layer has a thickness of 6 μm or less.

5. A silicon platform for optical modules according to claim 1, wherein optical elements are mounted and an end portion of the second conductor layer lies right below the optical elements.
6. A silicon platform for optical modules according to claim 1, wherein a bulky portion is formed on part of the first insulating layer.
7. A silicon platform for optical modules according to claim 1, wherein the first conductor layer, the second insulating layer and the second conductor layer constitute a microstrip line structure.
8. A silicon platform for optical modules according to claim 1, wherein the second conductor layer constitutes a coplanar distribution constant circuit structure. *RC line*
9. A silicon platform for optical modules according to claim 1, which is electrically connected to a driver IC by lead wires.
10. A silicon platform for optical modules according to claim 1, wherein at least one of a light emitting element and a light-receiving element are mounted.
11. A silicon platform for optical modules according to claim 1,

wherein the first insulating layer is an oxide layer.

12. A silicon platform for optical modules according to claim 1, wherein the first insulating layer is an SiO_2 insulating layer.

13. A silicon platform for optical modules according to claim 1, wherein the second insulating layer is a resin layer.

14. A silicon platform for optical modules according to claim 1, wherein the second insulating layer is a polyimide layer.